# **Low Noise Transistors PNP Silicon**

### **MAXIMUM RATINGS**



# **ON Semiconductor®**

Collector - Emitter Voltage   V <sub>CEO</sub> 30   -45   Vdc     Collector - Base Voltage   V <sub>CBO</sub> 30   -50   Vdc     Emitter - Base Voltage   V <sub>EBO</sub> 5.0   Vdc     Collector Current Continuous   I <sub>C</sub> -100   mAdc     Total Device Dissipation @   P   625   mW/°C     Total Device Dissipation @   P   625   mW/°C     Total Device Dissipation @   P   1.5   mW/°C     Total Device Dissipation @   P   0   0     Total Device Dissipation @   P   0   0     Total Device Dissipation @   P   0   0     Total Device Dissipation @   TJ, Tstg   -55 to +150   °C     Operating and Storage Junction TJ, Tstg   -55 to +150   °C   °C     Thermal Resistance, Junction to Case   Rejue   83.3   °C/W   °C     Thermal Resistance, Junction to Case   Rejue   83.3   °C/W   °C     Set Operation to Case   Rejue   83.3   °C/W   °C   °C	Rating	Symbol	BC559	BC560	Unit	http://onsemi.com
Emitter - Base Voltage $V_{EBO}$ -5.0VdcCollector Current ContinuousI_C-100mAdcTotal Device Dissipation @ T_A = 25°CPDmWTotal Device Dissipation @ T_C = 25°CPD625 5.0mW/°CTotal Device Dissipation @ T_C = 25°CPDWatt 1.5 12CASE 29-04, STYLE 17 TO-92 (TO-226AA)Operating and Storage Junction Temperature RangeTJ, T_{stg}-55 to +150°CClaracteristicSymbolMaxUnit °C/WThermal Resistance, Junction to AmbientReJA200°C/WThermal Resistance, Junction to CaseReJA83.3°C/W	Collector - Emitter Voltage	V <sub>CEO</sub>	-30	-45	Vdc	• • • • • • • • • • • • • • • • • • • •
Collector Current — ContinuousIc-100mAdcTotal Device Dissipation @ T_A = 25°CPDmWDerate above 25°C625mW/°CTotal Device Dissipation @ T_C = 25°CPDWattTotal Device Dissipation @ T_C = 25°CPDWattTotal Device Dissipation @ T_C = 25°CPDWattTotal Device Dissipation @ T_G = 25°CPDWattTotal Device Dissipation @ T_G = 25°CPDWattTotal Device Dissipation @ T_G = 25°CPDCASE 29-04, STYLE 17 TO-92 (TO-226AA)Operating and Storage Junction Temperature RangeTJ, T_stg-55 to +150CharacteristicSymbolMaxUnitThermal Resistance, Junction to AmbientReJA200CharacteristicSymbol83.3°C/WThermal Resistance, Junction to CaseReJC83.3CharacteristicSymbol83.3°C/W	Collector - Base Voltage	V <sub>CBO</sub>	-30	-50	Vdc	
Total Device Dissipation @ T_A = 25°CP DM 625mW mW/°CTotal Device Dissipation @ T_C = 25°CP D625mW/°CTotal Device Dissipation @ T_C = 25°CP DWatt12Operating and Storage Junction Temperature RangeT, T, Tstg-55 to +150°CCOLLECTORTHERMAL CHARACTERISTICSCharacteristicSymbolMaxUnitThermal Resistance, Junction to AmbientR <sub>0JA</sub> 200°C/WThermal Resistance, Junction to CaseR <sub>0JC</sub> 83.3°C/W	Emitter-Base Voltage	V <sub>EBO</sub>	-5	5.0	Vdc	
$T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ $B_D$ $625$ 5.0 $mW/^{\circ}C$ Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$ $P_D$ $Watt$ 1.5 12 $CASE 29-04, STYLE 17$ TO-92 (TO-226AA)Operating and Storage Junction Temperature Range $T_J, T_{stg}$ $-55$ to $+150$ $^{\circ}C$ Class 29-04, STYLE 17 TO-92 (TO-226AA)COLLECTOR1Thermal Resistance, Junction to AmbientRe, JA200 $^{\circ}C/W$ Thermal Resistance, Junction to Case $R_{\theta,JC}$ $83.3$ $^{\circ}C/W$ 3	Collector Current — Continuous	Ι <sub>C</sub>	-1	00	mAdc	
$T_{C} = 25^{\circ}C$ Derate above 25°C1.5 12 $MW/^{\circ}C$ Operating and Storage Junction Temperature RangeT, T, Tstg-55 to +150°CCharacteristicSymbolMaxUnitThermal Resistance, Junction to AmbientR_{0JA}200°C/W°CThermal Resistance, Junction to CaseR_{0JC}83.3°C/W3	$T_A = 25^{\circ}C$	P <sub>D</sub>				
Temperature Range Of org Of org Collector   THERMAL CHARACTERISTICS Thermal Resistance, Junction to Ambient Symbol Max Unit   Thermal Resistance, Junction to Ambient R <sub>θJA</sub> 200 °C/W °C/W   Thermal Resistance, Junction to Case R <sub>θJC</sub> 83.3 °C/W °C/W	$T_{\rm C} = 25^{\circ}{\rm C}$	P <sub>D</sub>				
Characteristic Symbol Max Unit   Thermal Resistance, Junction to Ambient R <sub>θJA</sub> 200 °C/W   Thermal Resistance, Junction to Case R <sub>θJC</sub> 83.3 °C/W		T <sub>J</sub> , T <sub>stg</sub>	-55 to	o +150	°C	
Thermal Resistance, Junction to Ambient R <sub>θJA</sub> 200 °C/W   Thermal Resistance, Junction to Case R <sub>θJC</sub> 83.3 °C/W	THERMAL CHARACTERISTIC	S				
Ambient BASE   Thermal Resistance, Junction to Case R <sub>θJC</sub> 83.3 °C/W	Characteristic	Symbol	м	ax	Unit	
Case 3		R <sub>θJA</sub>	20	00	°C/W	BASE
		R <sub>θJC</sub>	83			
ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25°C unless otherwise noted)		2	AIS ONT	C.MI		EWITTER

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = –10 mAdc, I <sub>B</sub> = 0) BC559 BC560	V <sub>(BR)CEO</sub>	-30 -45	_		Vdc
$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	V <sub>(BR)CBO</sub>	-30 -50			Vdc
Emitter – Base Breakdown Voltage ( $I_E = -10 \ \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_E = 0, T_A = +125^{\circ}\text{C})$	I <sub>CBO</sub>			-15 -5.0	nAdc μAdc
Emitter Cutoff Current ( $V_{EB} = -4.0 \text{ Vdc}, I_C = 0$ )	I <sub>EBO</sub>	—	_	-15	nAdc

## **BC559**

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic			Min	Тур	Max	Unit
ON CHARACTERISTICS		·				
DC Current Gain (I <sub>C</sub> = -10 $\mu$ Adc, V <sub>CE</sub> = -5.0 Vdc) (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc)	BC559B BC559C/560C BC559B BC559C/560C BC559	h <sub>FE</sub>	100 100 180 380 120	150 270 290 500	 460 800 800	
$      Collector - Emitter Saturation Voltage \\ (I_C = -10 mAdc, I_B = -0.5 mAdc) \\ (I_C = -10 mAdc, I_B = see note 1) \\ (I_C = -100 mAdc, I_B = -5.0 mAdc, see note 1) $	ote 2)	V <sub>CE(sat)</sub>		-0.075 -0.3 -0.25	-0.25 -0.6 	Vdc
Base-Emitter Saturation Voltage ( $I_c = -100 \text{ mAdc}$ , $I_B = -5.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	-	-1.1		Vdc
$\begin{array}{l} Base-Emitter \ On \ Voltage \\ (I_C = -10 \ \mu Adc, \ V_{CE} = -5.0 \ Vdc) \\ (I_C = -100 \ \mu Adc, \ V_{CE} = -5.0 \ Vdc) \\ (I_C = -2.0 \ mAdc, \ V_{CE} = -5.0 \ Vdc) \end{array}$		V <sub>BE(on)</sub>	  _0.55	-0.52 -0.55 -0.62	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS	6		•	, C	•	

Current – Gain — Bandwidth Product (I <sub>C</sub> = –10 mAdc, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)	fT		250	$\overline{h}$	MHz
Collector-Base Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cbo</sub>		2.5	_	pF
Small–Signal Current Gain (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 V, f = 1.0 kHz) BC559B BC559C/BC560C	h <sub>fe</sub>	240 450	330 600	500 900	—
Noise Figure ( $I_C = -200 \ \mu Adc$ , $V_{CE} = -5.0 \ Vdc$ , $R_S = 2.0 \ k\Omega$ , f = 1.0 kHz) ( $I_C = -200 \ \mu Adc$ , $V_{CE} = -5.0 \ Vdc$ , $R_S = 100 \ k\Omega$ , f = 1.0 kHz, $\Delta f = 200 \ kHz$ )	NF <sub>1</sub> NF <sub>2</sub>	_	0.5	2.0 10	dB
NOTES: 1. $I_B$ is value for which $I_C = -11$ mA at $V_{CE} = -1.0$ V. 2. Pulse test = 300 $\mu$ s – Duty cycle = 2%.					

## BC559

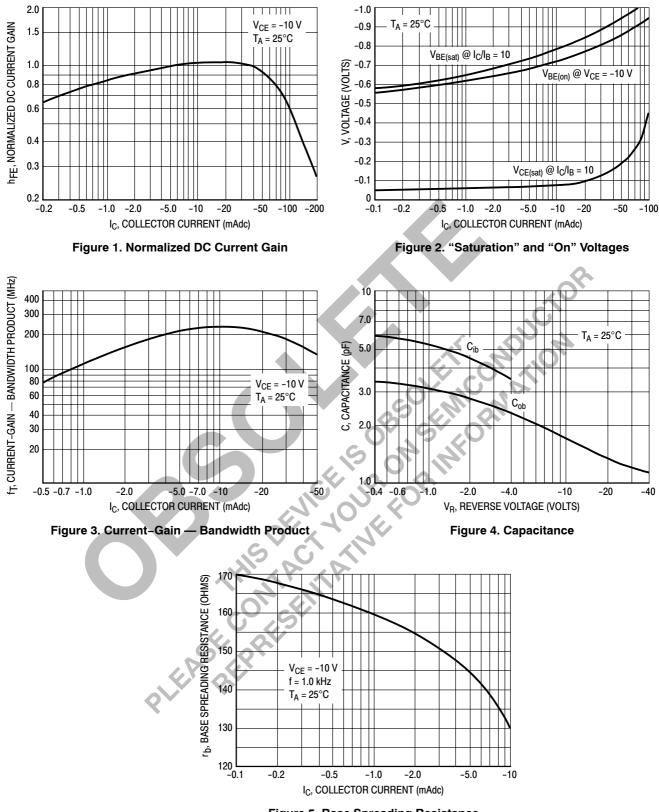
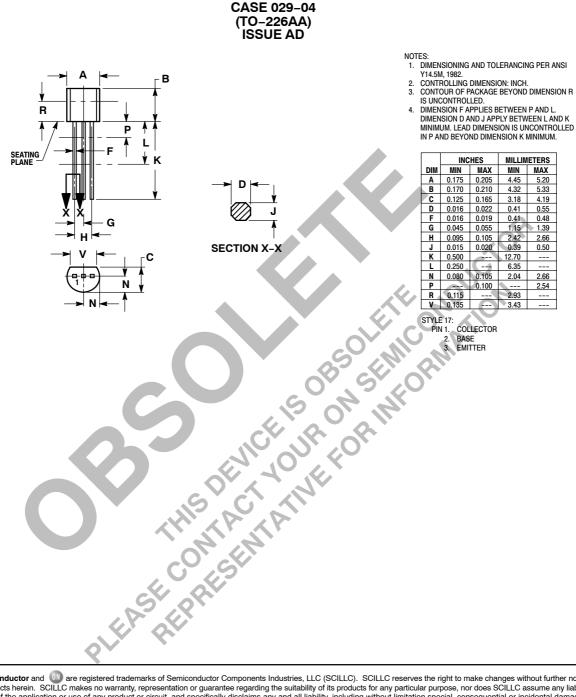


Figure 5. Base Spreading Resistance

#### BC559

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